

U.S. Serial No.: 10/652,314  
Amendment Under 37 C.F.R. §1.111 dated September 24, 2004  
Response to the Office Action of June 24, 2004

**In the Specification**

**Amend** page 1, line 3 of the specification to read as follows

CROSS-REFERENCE TO ~~PERATED~~ RELATED APPLICATION

**Amend** the paragraph beginning page 13, line 24 through page 14, line 7 to read as follows:

As described above, the resist application device according to the present embodiment suppresses the hydrolytic reaction of the HMDS to be used in the hydrophobic processing of the surface of the wafer 10, whereby the generation of foreign substances which are a cause for inconveniences, such as pattern defects, etc. on the surface of the wafer 10 with the resist developed can be suppressed. Furthermore, the adhesion between the wafer 10 and the resist film can be better. Thus, semiconductor devices of high quality can be fabricated with high yields.